

製品概要

NSS60200SMT: Single 60V 2A Low $V_{CE(sat)}$ PNP Transistor in WDFN6

技術情報は、データシートをご参照ください。

ON Semiconductor's e2PowerEdge family of low $V_{CE(sat)}$ transistors are miniature surface mount devices featuring ultra low saturation voltage ($V_{CE(sat)}$) and high current gain capability in a small form factor, 2x2mm plastic leadless package. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e2PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

特長

- -2A IDC, -3A ICM
- NSV60200SMTWTBG - Wettable Flanks Packaged Device
- Low $V_{CE(sat)}$: -0.45V @ -2A IC, IC/IB= 10
- Beta of 80 @ -2ADC, VCE = -2V
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

利点

- High Robustness
- Improved AOI Capability
- High Energy Efficiency
- High Gain Amplification

アプリケーション

- High Side Switching
- Overvoltage Protection

最終製品

- Automotive RCL and other lighting
- Automotive Airbag Deployment
- Automotive Instrument Clusters

電氣的仕様

製品	Pricing (\$/Unit)	Compliance	Status	Polarity	Type	$V_{CE(sat)}$ Max (V)	I_C Cont. (A)	V_{CEO} Min (V)	V_{CBO} (V)	V_{EBO} (V)	$V_{BE(sat)}$ (V)	$V_{BE(on)}$ (V)	h_{FE} Min	h_{FE} Max	f_T Min (MHz)	P_{TM} Max (W)	Package Type
NSS60200SMTTBG	0.172	Pb-free Halide free	Active	PNP	Low $V_{CE(sat)}$	0.45	2	60	60	6	1.1	0.9	40	-	155	1.8	WDFN-6
NSV60200SMTWTBG	0.18	AEC Qualified PPAP Capable Pb-free Halide free	Active	PNP	Low $V_{CE(sat)}$	0.45	2	60	60	6	1.1	0.9	40	-	155	1.8	WDFN-6

詳細は、弊社 www.onsemi.jp の営業または販売代理店にお問い合わせください。

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